

# Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Drain-Source Voltage	$V_{DSS}$	-20	V
Gate-Source Voltage	V <sub>GSS</sub>	±12	V
Drain Current (Note 5)	I <sub>D</sub>	-3.8	А
Pulsed Drain Current (Note 6)	I <sub>DM</sub>	-13	Α

## Thermal Characteristics (@ $T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P <sub>D</sub>	1.4	W
Thermal Resistance, Junction to Ambient	$R_{ hetaJA}$	89	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

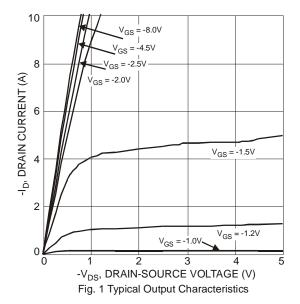
### Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

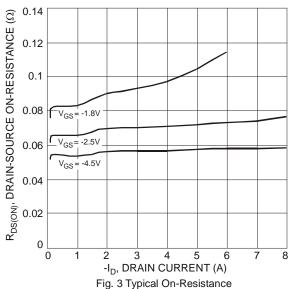
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7							
Drain-Source Breakdown Voltage	$BV_{DSS}$	-20			V	$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>		_	-1	μΑ	$V_{DS} = -20V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>			±100	nA	$V_{GS} = \pm 8V, V_{DS} = 0V$	
Gate-Source Leakage		_		±800		$V_{GS} = \pm 12V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	$V_{GS(th)}$	-0.45		-0.9	V	$V_{DS} = V_{GS}$ , $I_D = -250\mu A$	
		_	54	70		$V_{GS} = -4.5V$ , $I_D = -2.8A$	
Static Drain-Source On-Resistance	R <sub>DS (ON)</sub>	_	68	85	mΩ	$V_{GS} = -2.5V$ , $I_D = -2.0A$	
		_	86			$V_{GS} = -1.8V, I_D = -1.0A$	
Forward Transfer Admittance	Y <sub>fs</sub>	_	8		S	V <sub>DS</sub> = -5V, I <sub>D</sub> = -2.8A	
Diode Forward Voltage (Note 7)	$V_{SD}$	_	0.7	-1.2	V	$V_{GS} = 0V, I_{S} = -1.6A$	
DYNAMIC CHARACTERISTICS							
Input Capacitance	C <sub>iss</sub>		536	_	pF		
Output Capacitance	Coss	_	68	_	рF	V <sub>DS</sub> = -10V, V <sub>GS</sub> = 0V -f = 1.0MHz	
Reverse Transfer Capacitance	Crss	_	59	_	рF		
Gate Resistance	Rg	-	34	-	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge	$Q_{g}$	-	6.5	-	nC	15)/ )/ 40)/	
Gate-Source Charge	Qgs	-	8.0	-	nC	$V_{GS} = -4.5V, V_{DD} = -10V,$ $I_{D} = -1.5A$	
Gate-Drain Charge	$Q_{gd}$	-	1.4	-	nC		
Turn-On Delay Time	t <sub>D(on)</sub>	-	11.51	-	ns		
Turn-On Rise Time	t <sub>r</sub>	-	12.09	-	ns	$V_{GEN}$ = -4.5V, $V_{DD}$ = -10V, $R_L$ = 10 $\Omega$ , $R_G$ = 6 $\Omega$	
Turn-Off Delay Time	t <sub>D(off)</sub>	-	55.34	-	ns		
Turn-Off Fall Time	t <sub>f</sub>	-	27.54	-	ns		

Notes:

- Device mounted on FR-4 PCB, on minimum recommended, 2oz Copper pad layout.
  Repetitive rating, pulse width limited by junction temperature.
  Short duration pulse test used to minimize self-heating effect.







vs. Drain Current and Gate Voltage

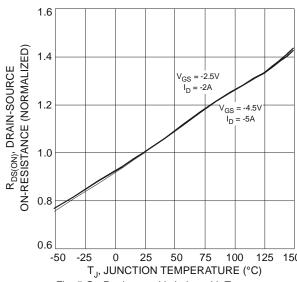


Fig. 5 On-Resistance Variation with Temperature

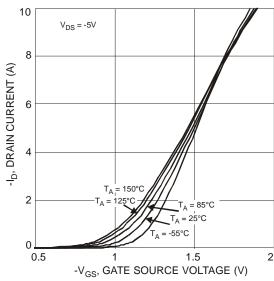


Fig. 2 Typical Transfer Characteristics

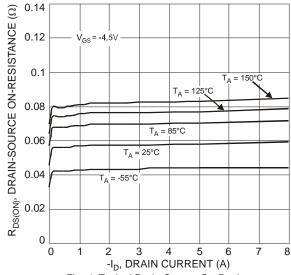


Fig. 4 Typical Drain-Source On-Resistance vs. Drain Current and Temperature

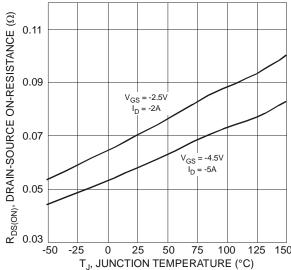
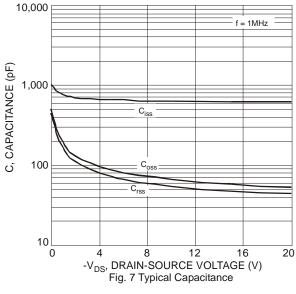
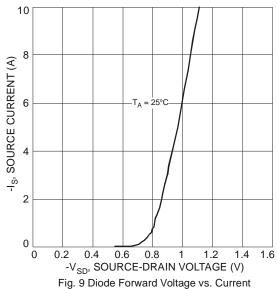
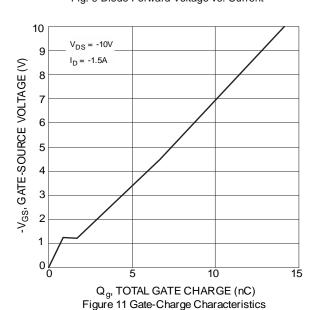


Fig. 6 On-Resistance Variation with Temperature









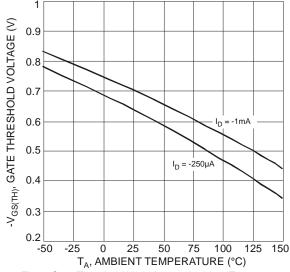


Fig. 8 Gate Threshold Variation vs. Ambient Temperature

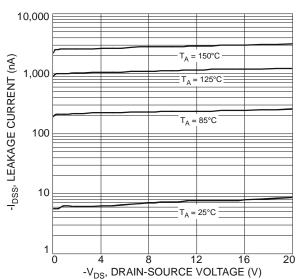


Fig. 10 Typical Drain-Source Leakage Current vs. Voltage



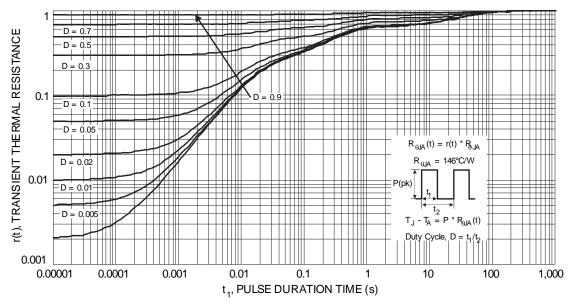
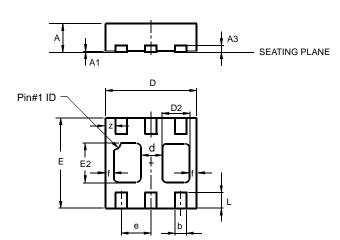


Fig. 12 Transient Thermal Response

### **Package Outline Dimensions**

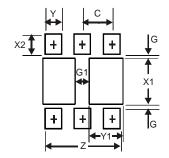
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



U-DFN2020-6					
Type B					
Dim	Min	Max	Тур		
Α	0.545	0.605	0.575		
A1	0	0.05	0.02		
A3			0.13		
b	0.20	0.30	0.25		
D	1.95	2.075	2.00		
d	_	_	0.45		
D2	0.50	0.70	0.60		
е			0.65		
Е	1.95	2.075	2.00		
E2	0.90	1.10	1.00		
f			0.15		
L	0.25	0.35	0.30		
Z	_	_	0.225		
All Dimensions in mm					

## **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	1.67
G	0.20
G1	0.40
X1	1.0
X2	0.45
Υ	0.37
Y1	0.70
С	0.65



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